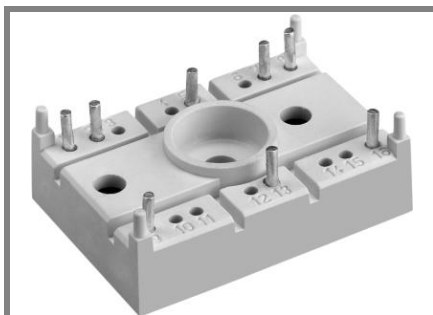


# SK 70 B



SEMITOP® 2

## Bridge Rectifier

### SK 70 B

#### Preliminary Data

#### Features

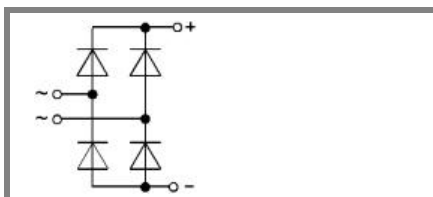
- Compact design
- One screw mounting
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DCB)
- Up 1600V reverse voltage
- High surge current
- Glass passivated diode chips
- UL recognized, file no. E 63 532

#### Typical Applications

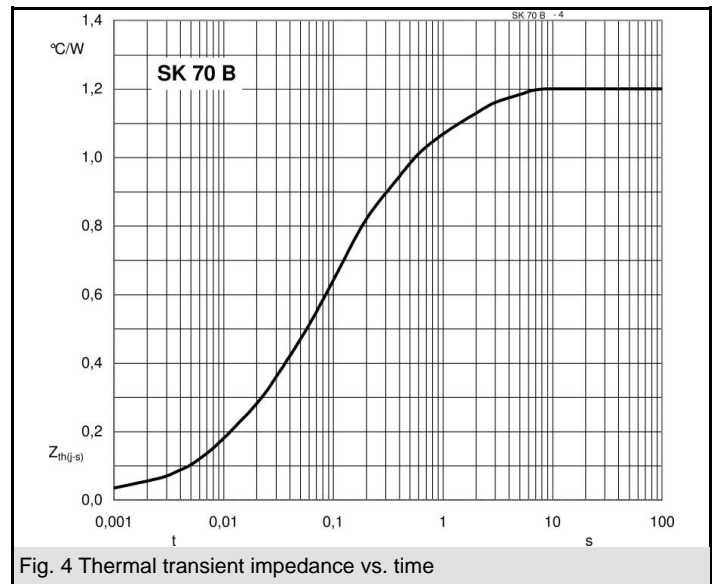
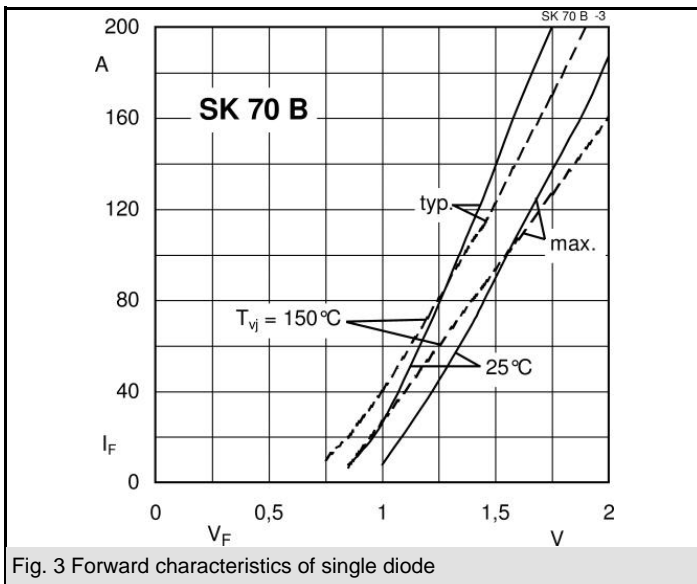
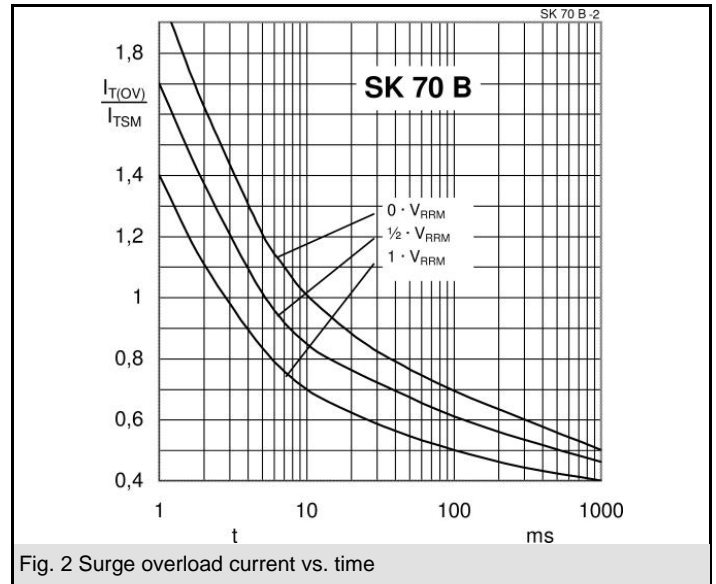
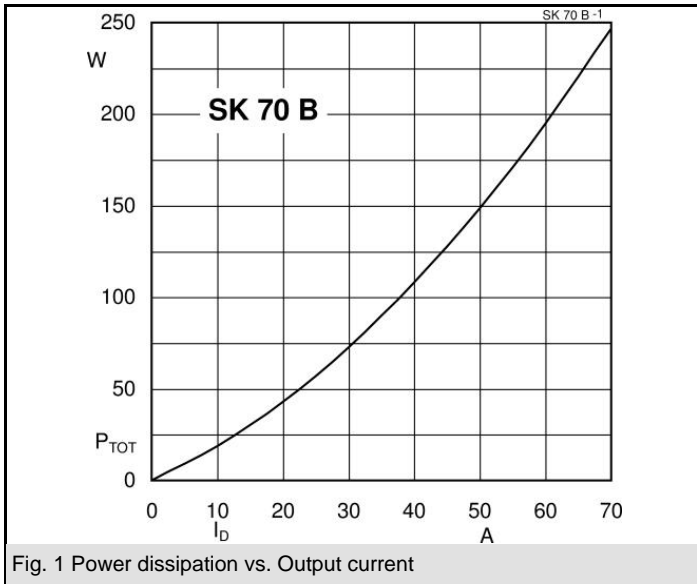
- Input rectifier for power supplies
- Rectifier

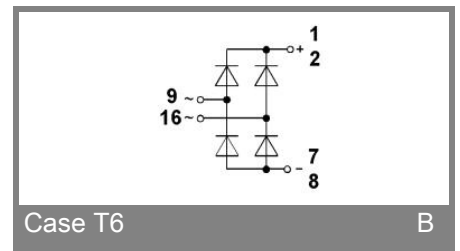
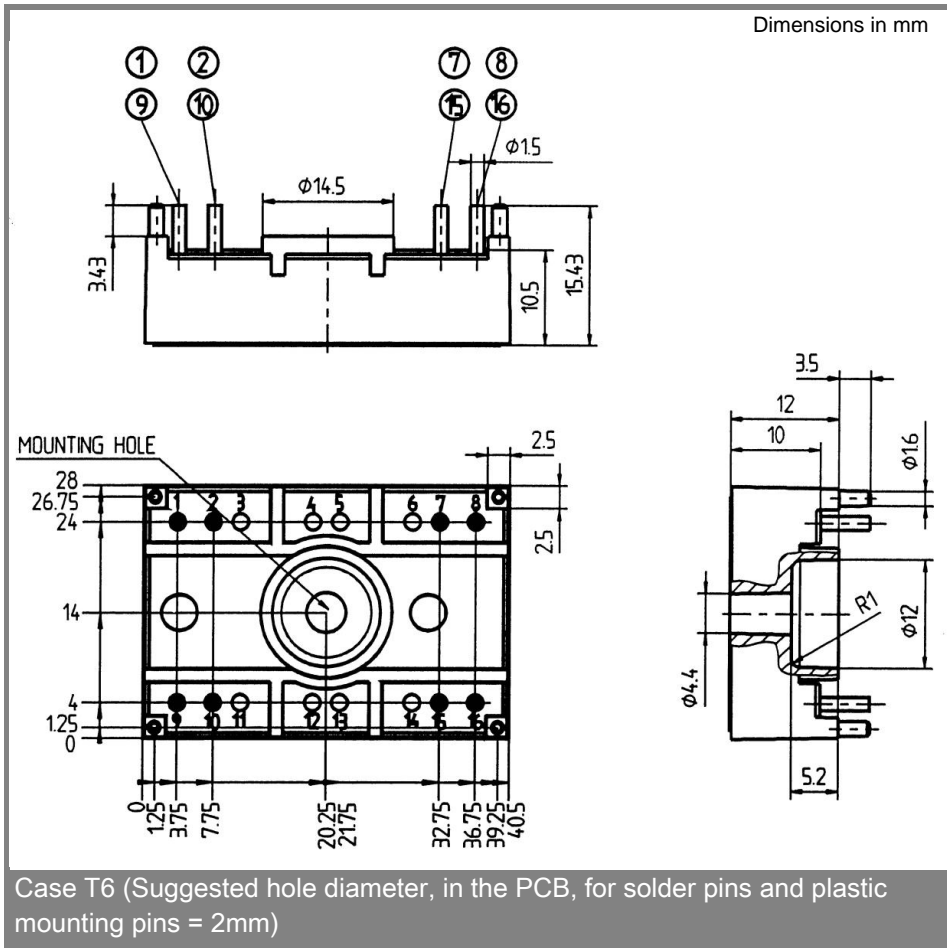
$V_{RSM}$ V	$V_{RRM}, V_{DRM}$ V	$I_D = 68 \text{ A (full conduction)}$ ( $T_s = 80 \text{ °C}$ )
800	800	SK 70 B 08
1200	1200	SK 70 B 12
1600	1600	SK 70 B 16

Symbol	Conditions	Values	Units
$I_D$	$T_s = 80 \text{ °C}$	68	A
$I_{FSM}$	$T_{vj} = 25 \text{ °C}; 10 \text{ ms}$ $T_{vj} = 125 \text{ °C}; 10 \text{ ms}$	700 560	A A
$i^2t$	$T_{vj} = 25 \text{ °C}; 8,3...10 \text{ ms}$ $T_{vj} = 125 \text{ °C}; 8,3...10 \text{ ms}$	2450 1370	A <sup>2</sup> s A <sup>2</sup> s
$V_F$	$T_{vj} = 25 \text{ °C}; I_F = 35 \text{ A}$	max. 1,2	V
$V_{(TO)}$	$T_{vj} = 125 \text{ °C}$	max. 0,8	V
$r_T$	$T_{vj} = 125 \text{ °C}$	max. 11	mΩ
$I_{RD}$	$T_{vj} = 150 \text{ °C}; V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$	max. 4	mA mA
$R_{th(f-s)}$	per diode per module	1,2 0,3	K/W K/W
$T_{solder}$	terminals, 10s	260	°C
$T_{vj}$		-40...+150	°C
$T_{stg}$		-40...+125	°C
$V_{isol}$	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 ( 2500 )	V
$M_s$	mounting torque to heatsink	2	Nm
$M_t$			
m	approx. weight	19	g
Case	SEMITOP® 2	T 6	



B





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